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2N5954-2N5956, 2N6372-2N6374, 2N6465-2N6468, 40829-40831 Silicon N-P-N and P-N-P Medium-Power Transistors

General-Purpose Types for Switching Applications

2N5954, -2N5955, and -2N5956 are multiple-epitaxial p-n-p transistors. 2N6372, -2N6373, and -2N6374 are multiple-epitaxial n-p-n transistors. They are complements to 2N5954, 2N5955, and 2N5956.

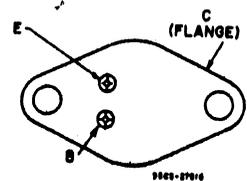
The 2N6465 and 2N6466 are multiple-epitaxial n-p-n transistors. They are complements to the 2N6467, and 2N6468, multiple-epitaxial p-n-p transistors. These devices differ in voltage ratings and in the currents at which the parameters are controlled.

All are supplied in the JEDEC TO-66 package.

Features:

- 2N5954-2N5956 complements to 2N6372-2N6374
- 2N6465, 2N6466 complements to 2N6467, 2N6468
- Low saturation voltages
- Maximum-safe-area-of-operation curves
- Thermal-cycle ratings
- Hermetically-sealed JEDEC TO-66 package

TERMINAL DESIGNATIONS

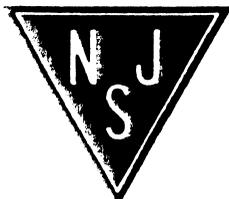


JEDEC TO-66

2N5954-2N5956 2N6372-2N6374, 2N6465-2N6468

MAXIMUM RATINGS, Absolute-Maximum Values:

	N-P-N 2N6374	2N6373	2N6372	2N6465	2N6466
	P-N-P 2N5956 [†] 40831 [†]	2N5955 [†] 40830 [†]	2N5954 [†] 40829 [†]	2N6467 [†]	2N6468 [†]
V _{CEO}	50	70	90	110	130 V
V _{CEX} (sus) V _{BE} = -1.5 V, R _{BE} = 100 Ω	50	70	90	110	130 V
V _{CER} (sus) R _{BE} = 100 Ω	45	65	85	105	125 V
V _{CEO} (sus)	40	60	80	100	120 V
V _{ESD}	5	5	5	5	5 V
I _C	6	6	6	4	4 A
I _B	2	2	2	2	2 A
T _J					
At T _C up to 25°C	40	40	40	40	40 W
	(2N6374) (2N5956)	(2N6373) (2N5955)	(2N6372) (2N5954)		
At T _A up to 25°C	5.8	5.8	5.8	-	- W
	(40831)	(40830)	(40829)		
At T _C above 25°C	Derate linearly to 200°C				
T _J , T _{mg}	-65 to +200 °C				
T _L					
At distance ≥ 1/32 in. (0.8 mm) from seating plane for 10 s max.	+235 °C				



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that data-sheets are current before placing orders.

2N6465-2N6468, 40829-40831

2N5954-2N5956, 2N6372-2N6374,

ELECTRICAL CHARACTERISTICS, At Case Temperature (T_C) = 25°C unless otherwise specified

CHARACTERISTIC	TEST CONDITIONS				LIMITS						UNITS
	VOLTAGE V dc		CURRENT A dc		2N6374 2N5956 40831		2N6373 2N5955 40830		2N6372 2N5954 40829		
	V _{CE}	V _{BE}	I _C	I _B	Min.	Max.	Min.	Max.	Min.	Max.	
I _{CE} R _{BE} =100 Ω	35 55 75				-	100	-	-	-	-	μA
I _C _{EX} R _{BE} =100 Ω	45 65 85	-1.5 -1.5 -1.5			-	100	-	-	-	-	μA
R _{BE} =100 Ω, T _C =150°C	45 65 85	-1.5 -1.5 -1.5			-	2	-	-	-	-	mA
I _{CEO}	25 45 65				-	1	-	-	-	-	mA
I _{EBO}		-5			-	0.1	-	0.1	-	0.1	mA
h _{FE}	4		3 ^a		20	100	-	-	-	-	
	4		2.5 ^a		-	-	20	100	-	-	
	4		2 ^a		-	-	-	-	20	100	
	4		6 ^a		5	-	5	-	5	-	
V _{CEO(sus)}			0.1 ^a		40 ^b	-	60 ^b	-	80 ^b	-	V
V _{CER(sus)} R _{BE} =100 Ω			0.1 ^a		45 ^b	-	65 ^b	-	85 ^b	-	
V _{CEX(sus)} R _{BE} =100 Ω		-1.5	0.1 ^a		50 ^b	-	70 ^b	-	90 ^b	-	
V _{BE}	4		3 ^a		-	2	-	-	-	-	V
	4		2.5 ^a		-	-	-	2	-	-	
	4		2 ^a		-	-	-	-	-	2	
	4		6 ^a		-	3	-	3	-	3	
V _{CE(sat)}			3 ^a	0.3 ^c	-	1	-	-	-	-	V
			2.5 ^a	0.25	-	-	-	1	-	-	
			2 ^a	0.2	-	-	-	-	-	1	
h _{fe} f=1 MHz	4		1		4	-	4	-	4	-	
	4	-4	-1		5	-	5	-	5	-	
h _{fe} f=1 kHz	4		0.5		25	-	25	-	25	-	
R _{θJC} 2N5954-56, 2N6372-74					-	4.3	-	4.3	-	4.3	°C/W
R _{θJA} 40829-40831					-	30	-	30	-	30	

ELECTRICAL CHARACTERISTICS, At Case Temperature (T_C) = 25°C
unless otherwise specified

CHARACTERISTIC	TEST CONDITIONS				LIMITS				UNITS
	VOLTAGE V dc		CURRENT A dc		2N6465 2N6467 [♦]		2N6486 2N6468 [♦]		
	V _{CE}	V _{BE}	I _C	I _B	Min.	Max.	Min.	Max.	
I _{CER} R _{BE} = 100 Ω	95 100				-	100	-	-	μA
I _{CEX} R _{BE} = 100 Ω	100 120	-1.5 -1.5			-	100	-	-	μA
R _{BE} = 100 Ω, T _C = 150°C	100 120	-1.5 -1.5			-	2	-	-	mA
I _{CEO}	50 60				-	1	-	-	mA
I _{EBO}		-5			-	0.1	-	0.1	mA
h _{FE}	4 4		1.5 ^a 4 ^a		15 5	150 -	15 5	150 -	
V _{CEO(sus)}			0.1 ^a		100 ^b	-	120 ^b	-	V
V _{CER(sus)} R _{BE} = 100 Ω			0.1 ^a		105 ^b	-	125 ^b	-	
V _{CEX(sus)} R _{BE} = 100 Ω		-1.5	0.1 ^a		110 ^b	-	130 ^b	-	
V _{BE}	4 4		1.5 ^a 4 ^a		- -	2 3.5	- -	2 3.5	V
V _{CE(sat)}			1.5 ^a 4 ^a -4 ^a	0.15 0.8 -0.8	- - -	1.2 3* -4*	- - -	1.2 3* -4*	V
h _{fe} f = 1 MHz	4		1		5	-	5	-	
h _{fe} f = 1 kHz	4		0.5		25	-	25	-	
R _{θJC}					-	4.3	-	4.3	°C/W

^a In accordance with JEDEC registration data format JS-6 RDF-2.

[♦] For p-n-p devices, voltage and current values are negative.

[▪] Pulsed, pulse duration = 300 μs, duty factor = 1.8%

^b CAUTION: Sustaining voltages V_{CEO(sus)}, V_{CER(sus)}, and V_{CEX(sus)} MUST NOT be measured on a curve tracer.

